	Туре	L#	Hits	Search Text	DBs	Time Stamp	C o m e nt	D	Er ro
1	BRS	L22	8	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:02			0
2	BRS	L23	2	"20020102852"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:08			0
3	BRS	L24	69	(TTHA) or "desferriferrioxamin B" or	USPAT; US-PGPUB; EPO; JPO;	2003/09/16 15:13			0
4	BRS	L25	4306	Tris[2-(N-hydroxycarbomyl)ethyl]-1,3,5-ben	USPAT; US-PGPUB; EPO; JPO;	2003/09/16 15:13			0
5	BRS	L26	1319	(TTHA) or "desferriferrioxamin B" or "N,N,N Tris[2-(N-hydroxycarbomyl)ethyl]-1,3,5-ben	USPAT; US-PGPUB; EPO; JPO;	2003/09/16 15:47			0
6	BRS	L27	886	26 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:10			0 .

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	Туре	L#	Hits	Search Text	DBs	Time Stamp	o m m	ef in	Er ro rs
7	BRS	L49	21	27 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:11			0
8	IS&R	L50	2	("4,554,050").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:47			0
9	BRS	L51	114	27 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 15:51			0
10	BRS	L52	221	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3) same (dissolv\$4) same (helium or He or argon or Ar or nitrogen or "N.sub.2" or oxygen or "O.sub.2" or ozone or "O.sub.3" or hydrogen or "H.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:17			0
11	BRS	L53	126	52 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:18			0
12	BRS	L55	4	53 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:19			0
13	BRS	L54	19	53 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:19			0
14	BRS	L56	1831	((etch\$3 or clean\$3) with (dissolv\$4) with (helium or He or argon or Ar or nitrogen or "N.sub.2" or oxygen or "O.sub.2" or ozone or "O.sub.3" or hydrogen or "H.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:17			0

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	Туре	L#	Hits	Search Text	DBs	Time Stamp	0 m m	ef in	Er ro
15	BRS	L57	1153	56 and @pd<=20000626	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:18			0
16	BRS	L59	117	57 and 134/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:28			0
17	BRS	L58	87 _.	57 and 438/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	: 4 (2 : 4 ()			0
18	BRS	L60	1066	57 not 58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 16:28			0
19	BRS	L61	108	59 not 58	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:01			0
20	BRS	L62	1	(spin\$4 with (wafer or semiconductor or substrate)) same (etch\$3 or clean\$3) same (degas\$3 with (water or "H.sub.2O"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17:13			0
21	BRS	L63	38	(wafer or semiconductor or substrate))same (etch\$3 or clean\$3) same (degas\$3 with (water or "H.sub.2O")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/16 17: <u>1</u> 3			0